

214505US-8-PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

YUICHI WATANABE

: ATTN: APPLICATION DIVISION

SERIAL NO: NEW U.S. PCT APPLN
(Based on PCT/JP01/00885)

FILED: HERewith

: EXAMINER:

FOR: APPARATUS AND CIRCUIT FOR :
POWER SUPPLY, AND APPARATUS
FOR CONTROLLING LARGE CURRENT
LOAD

#6
Prejudgments
Chilton
4-4-01

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified
application as follows:

IN THE SPECIFICATION

Page 8, beginning lines 2-16, delete the existing paragraph and replace it with the
following paragraph:

In this control apparatus, however, the power MOS-FET used as the switching
element of on/off control generates much heat. Therefore, it is necessary to perform the
radiation design accurately. A channel temperature Tch max of the power MOS-FET is
calculated as

$$Tch \max = (Ta \max) + (Ron \max) \times (Io \max)$$

$$\times (Io \max) \times Rth (ch-a)$$

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